



C. Material Growth & Characterization 분과

2019년 2월 14일(목), 09:00-10:45

Room G (루비3, 5층)

[TG1-C] Oxide (Nitride) Materials

좌장: 송진동 책임연구원(KIST), 김태현 교수(울산대학교)

<p>TG1-C-1 09:00-09:15</p>	<p>β-Ga₂O₃ Thin Films for Power Semiconductor Device by Pulsed Laser Deposition Hyung-Jin Choi, Shin-Ik Kim, and Seung-Hyub Baek <i>KIST</i></p>
<p>TG1-C-2 09:15-09:45</p>	<p>[초청] Ultra Wide Band Gap Gallium Oxide for Power Semiconductor Applications: Current Status, Properties, Its MBE Growth and Characterization Soon-Ku Hong, Trong Si Ngo, Duc Duy Le, and Jungkuk Lee <i>Department of Materials Science and Engineering, Chungnam National University</i></p>
<p>TG1-C-3 09:45-10:00</p>	<p>Atomic-Scale Crystal Patterning in the Oxide Film by the Electron Beam Irradiation Gwangyeob Lee^{1,2}, Gyeongtak Han³, Shin-Ik Kim⁴, Young-Min Kim^{3,5}, Seung-Hyub Baek⁴, Do Hyang Kim², and Hye Jung Chang¹ <i>¹Advanced Analysis Center, KIST, ²Department of Materials Science and Engineering, Yonsei University, ³Department of Energy Science, Sungkyunkwan University, ⁴Electronic Materials Research Center, KIST, ⁵IBS Center for Integrated Nanostructure Physics, Institute for Basic Science</i></p>
<p>TG1-C-4 10:00-10:15</p>	<p>In-Situ TEM Electrical Biasing of LAO/STO Interface-Devices Revealing Charge Modulation and Associated Structural and Chemical Changes Jinsol Seo¹, Bumsu Park^{1,2}, Christoph T. Koch³, Hyungwoo Lee⁴, Chang-Beom Eom⁴, and Sang Ho Oh¹ <i>¹Department of Energy Science, Sungkyunkwan University, ²Center for Nano Tubes and Nanostructured Composites, Sungkyunkwan University, ³Department of Physics, Humboldt University of Berlin, Germany, ⁴Department of Materials Science and Engineering, University of Wisconsin-Madison, USA</i></p>
<p>TG1-C-5 10:15-10:30</p>	<p>Electron Exchange Process Control between Silver Nanoparticles and Metal-Oxides for Highly Selective Gas Detection Yeong Min Kwon, Tae Won Lee, Hee Jun Kim, and Jeong Min Baik <i>School of Materials Science and Engineering, KIST-UNIST-Ulsan Center for Convergent Materials, UNIST</i></p>
<p>TG1-C-6 10:30-10:45</p>	<p>Structural Characterizations of Initial Treatment on Sapphire Substrate before the Growth of GaN By HVPE Chung-Seok Oh, Se-Hun Yeon, and Min-Seo Park <i>R&D Center, Han Sung S-Tec Co., Ltd</i></p>